In the Claims:

Please rewrite the claims as follows:

1. (Original) Reactive nanoparticular porogen based on cyclodextrin derivative of the following formula 1 to be used as a porogen,

$$Si(OR)_3$$

$$O O O O$$

$$O O$$

$$O O O$$

$$O O$$

$$O$$

wherein R represents the same or different C_{1-6} alkyl group, respectively, wherein n is an integer of 6 to 12.

- 2. (Original) In claim 1, said derivative is selected from the group consisting of hexakis(2,3,6-tri-O-(3-trimethoxysilylpropyl)- α -cyclodextrin), hexakis(2,3,6-tri-O-(3-triethoxysilylpropyl)- β -cyclodextrin), heptakis(2,3,6-tri-O-(3-triethoxysilylpropyl)- β -cyclodextrin), octakis(2,3,6-tri-O-(3-triethoxysilylpropyl)- γ -cyclodextrin), and octakis(2,3,6-tri-O-(3-trimethoxysilylpropyl)- γ -cyclodextrin).
- 3. (Original) A dielectric matrix manufactured by sol-gel reaction of a derivative of the following formula 1,

$$\begin{array}{c|c}
Si(OR)_3 \\
\hline
O & O \\
O & O \\
\hline
O & O$$

wherein R represents the same or different C_{1-6} alkyl groups, respectively and wherein n is an integer of 6 to 12.

4. (Original) A low dielectric film manufactured by thin-filming of said dielectric matrix, which is manufactured by sol-gel reaction of the following formula 1,

$$\begin{array}{c|c}
Si(OR)_{3} \\
\hline
O & O \\
\hline
O & O \\
\hline
O & O \\
\hline
N & O \\
\hline
O & O \\
\hline
O & O \\
\hline
N & O \\
\hline
O & O \\
\hline
O$$

wherein R represents the same or different C_{1-6} alkyl groups respectively and n is an integer of 6 to 12.

- 5. (Original) In claim 4, said dielectric matrix comprises a silicate precursor selected from polymethylsilsequioxane and polymethylsilsequioxane copolymer.
- 6. (Original) An ultralow dielectric composition comprising:
 - a) an organic or inorganic silicate precursor, and
- b) a reactive nanoparticular porogen based on cyclodextrin derivative of the following formula 1,

$$(RO)_3Si \qquad Si(OR)_3$$

$$Si(OR)_3$$

$$Si(OR)_3$$

$$(1)$$

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wherein R represents the same or different C_{1-6} alkyl group, respectively and n is an integer of 6 to 12.

- 7. (Original) In claim 6, said ultralow dielectric composition is obtained by combining (a) said organic or inorganic silicate precursor and (b) said nanoparticle of a cyclodextrin derivative of the above formula 1, which are dissolved to have the equal concentration within the range of from 10 to 40 wt.%, with a mixing ratio of 10-50: 10-50 vol.% between the two solutions.
- 8. (Original) In claim 6, said derivative of the above formula 1 is an ultralow dielectric composition selected from the group consisting of hexakis(2,3,6-tri-O-(3-trimethoxysilylpropyl)- α -cyclodextrin), hexakis(2,3,6-tri-O-(3-triethoxysilylpropyl)- β -cyclodextrin), heptakis(2,3,6-tri-O-(3-triethoxysilylpropyl)- β -cyclodextrin), heptakis(2,3,6-tri-O-(3-triethoxysilylpropyl)- β -cyclodextrin), octakis(2,3,6-tri-O-(3-triethoxysilylpropyl)- γ -cyclodextrin), and octakis(2,3,6-tri-O-(3-trimethoxysilylpropyl)- γ -cyclodextrin).
- 9. (Original) In claim 6, said dielectric matrix comprises a silicate precursor selected from polymethylsilsequioxane and polymethylsilsequioxane copolymer.
- 10. (Currently Amended) An ultralow dielectric films manufactured by thin-filming of any one of the ultralow dielectric empositions of claims 6—9 composition of claim 6, wherein the porosity is 21 to 51% and dielectric constant is 2.1 to 1.54 when the relative volume of the template solution with reference to the matrix solution is 40 to 49%.
- 11. (New) An ultralow dielectric films manufactured by thin-filming of any one of the ultralow dielectric composition of claim 7, wherein the porosity is 21 to 51% and dielectric constant is 2.1 to 1.54 when the relative volume of the template solution with reference to the matrix solution is 40 to 49%.
- 12. (New) An ultralow dielectric films manufactured by thin-filming of any one of the ultralow dielectric composition of claim 8, wherein the porosity is 21 to 51% and dielectric constant is 2.1

to 1.54 when the relative volume of the template solution with reference to the matrix solution is 40 to 49%.

13. (New) An ultralow dielectric films manufactured by thin-filming of any one of the ultralow dielectric composition of claim 9, wherein the porosity is 21 to 51% and dielectric constant is 2.1 to 1.54 when the relative volume of the template solution with reference to the matrix solution is 40 to 49%.

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